

GM4132

NPN EPITAXIAL PLANAR TRANSISTOR

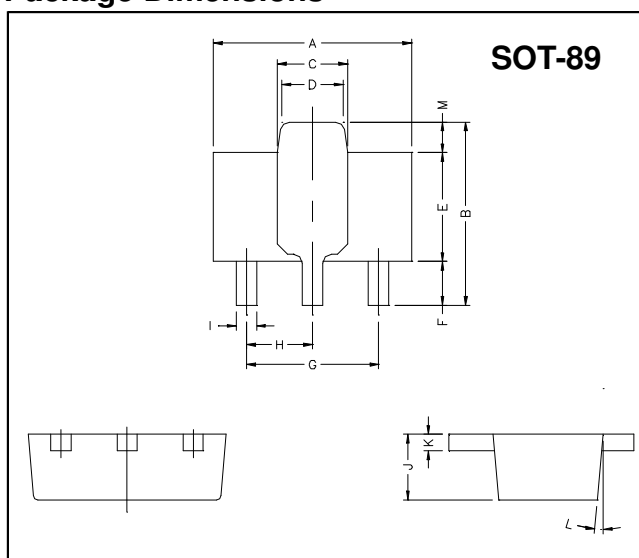
Description

The GM4132 is designed for power amplifier applications.

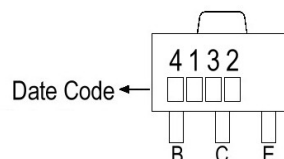
Features

- High breakdown voltage ($BV_{CEO}=120V$)
- Low collector output capacitance (Typ. 20pF at $V_{CB}=10V$)
- High transition frequency ($f_T=80MHz$)

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-55~+150	$^\circ C$
Collector to Base Voltage	V_{CB0}	120	V
Collector to Emitter Voltage	V_{CEO}	120	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current (DC)	I_C	2	A
Collector Current (Pulse 10ms)	I_C	3	A
Total Power Dissipation	P_D	1.2	W

Electrical Characteristics ($T_a = 25^\circ C$, unless otherwise stated)

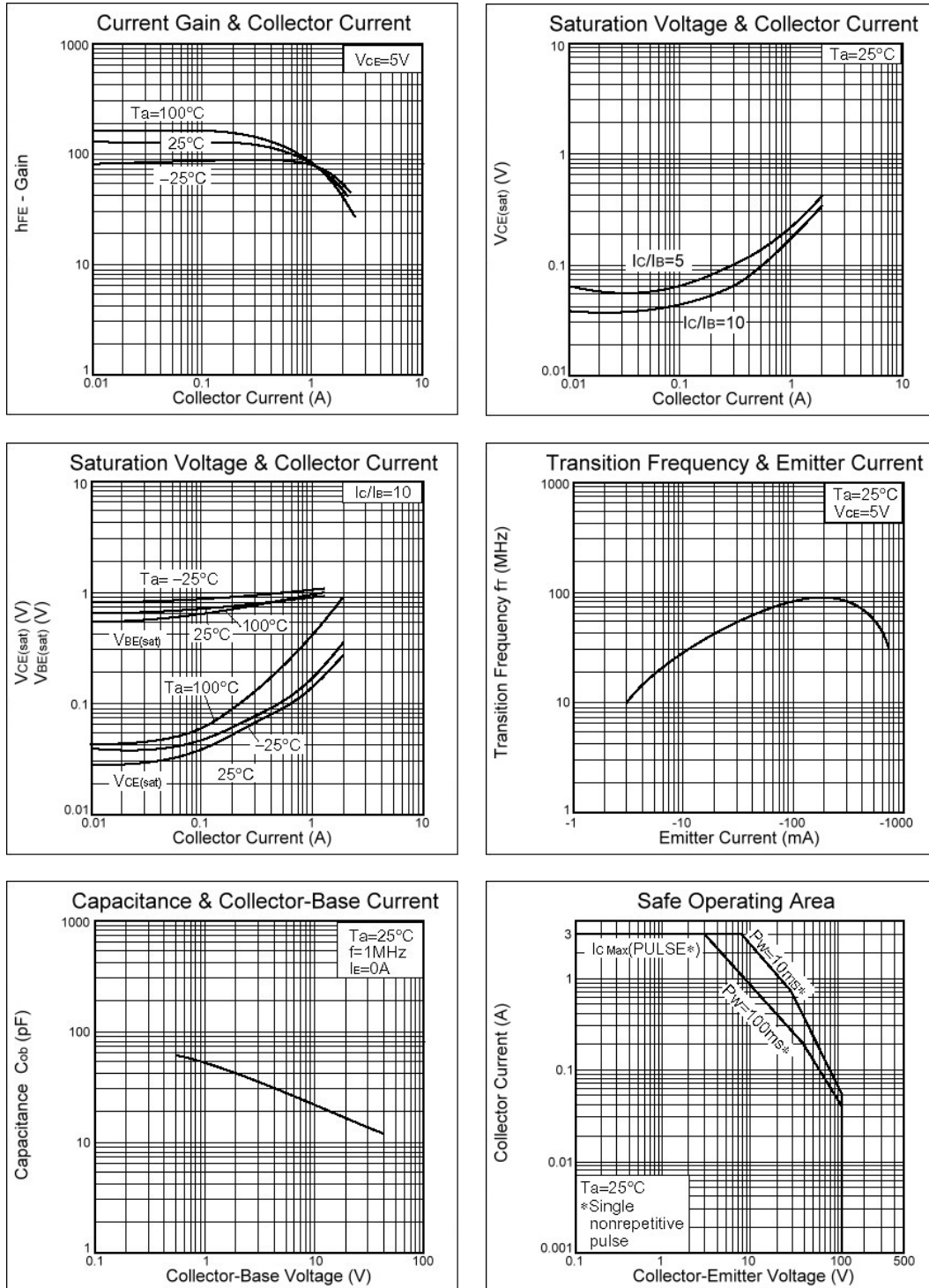
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CB0}	120	-	-	V	$I_C=50\mu A$, $I_E=0$
BV_{CEO}	120	-	-	V	$I_C=1mA$, $I_B=0$
BV_{EBO}	5	-	-	V	$I_E=50\mu A$, $I_C=0$
I_{CBO}	-	-	1	μA	$V_{CB}=100V$, $I_E=0$
I_{EBO}	-	-	1	μA	$V_{EB}=4V$, $I_C=0$
* $V_{CE(sat)}$	-	-	400	mV	$I_C=1A$, $I_B=100mA$
* h_{FE}	82	-	390		$V_{CE}=5V$, $I_C=100mA$
f_T	-	80	-	MHz	$V_{CE}=5V$, $I_E=100mA$, $f=30MHz$
C_{ob}	-	20	-	pF	$V_{CB}=10V$, $I_E=0$, $f=1MHz$

* Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of h_{FE}

Rank	P	Q	R
Range	82 ~ 180	120 ~ 270	180 ~ 390

Characteristics Curve



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